STD2N95K5, STF2N95K5, STP2N95K5, STU2N95K5

N-channel 950 V, 4.2 Ω typ., 2 A Zener-protected SuperMESH™ 5 Power MOSFETs in DPAK, TO-220FP, TO-220 and IPAK packages

Datasheet - production data

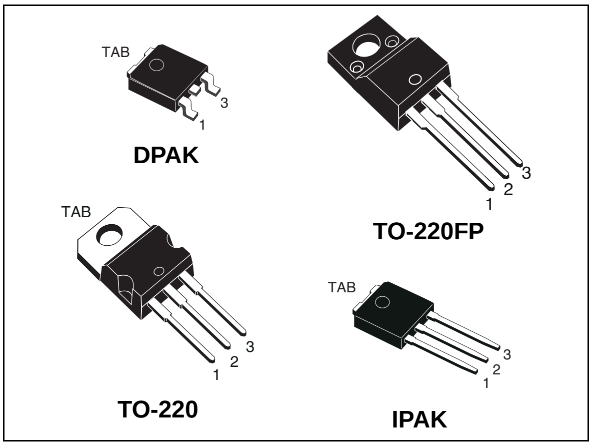
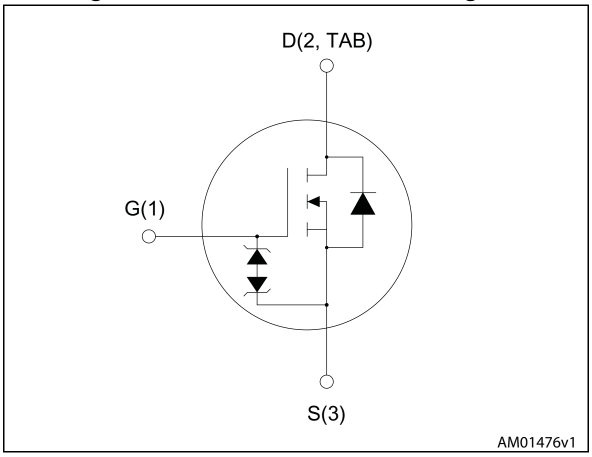


Figure 1. Internal schematic diagram



Features

Order codes	V_{DS}	$R_{DS(on)}$ max	I_D	P_{TOT}
STD2N95K5	950 V	5 Ω	2 A	45 W
STF2N95K5				20 W
STP2N95K5				45 W
STU2N95K5				

- TO-220 worldwide best $R_{DS(on)}$
- Worldwide best FOM (figure of merit)
- Ultra low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

These N-channel Zener-protected Power MOSFETs are designed using ST's revolutionary avalanche-rugged very high voltage SuperMESH™ 5 technology, based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance, and ultra-low gate charge for applications which require superior power density and high efficiency.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STD2N95K5	2N95K5	DPAK	Tape and reel
STF2N95K5		TO-220FP	Tube
STP2N95K5		TO-220	
STU2N95K5		IPAK	

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220FP	DPAK, TO-220, IPAK	
V_{GS}	Gate- source voltage	30		V
I_D	Drain current (continuous) at T_C = 25 °C	2[(1)]	2	A
I_D	Drain current (continuous) at T_C = 100 °C	1.3[(1)]	1.3	A
I_{DM} [(2)]	Drain current (pulsed)	8		A
P_{TOT}	Total dissipation at T_C = 25 °C	20	45	W
I_{AR}	Max current during repetitive or single pulse avalanche	1		A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D=I_{AS}, V_{DD}= 50 V)	50		mJ
dv/dt [(3)]	Peak diode recovery voltage slope	4.5		V/ns
dv/dt[(4)]	MOSFET dv/dt ruggedness	50		V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T_C=25 °C)	2500		V
T_j T_{stg}	Operating junction temperature Storage temperature	- 55 to 150		°C

1. Limited by maximum junction temperature
2. Pulse width limited by safe operating area.
3. I_{SD} ≤ 2 A, di/dt ≤ 100 A/μs, $V_{Peak} \leq V_{(BR)DSS}$.
4. $V_{SD} \leq$ 760 V

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		TO-220FP	DPAK, TO-220, IPAK	
$R_{thj\text{-}case}$	Thermal resistance junction-case max	6.25	2.78	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient max	62.50		°C/W

2 Electrical characteristics

(Tcase =25 °C unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0	950			V
I_{DSS}	Zero gate voltage, V_{GS} = 0 drain current	V_{DS} = 950 V V_{DS} = 950 V, T_C=125 °C			1 50	µA µA
I_{GSS}	Gate-body leakage current	V_{GS} = ± 20 V; V_{DS}=0			10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 100 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 1 A		4.2	5	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} =100 V, f=1 MHz, V_{GS}=0	-	105	-	pF
C_{oss}	Output capacitance		-	9	-	pF
C_{rss}	Reverse transfer capacitance		-	0.5	-	pF
$C_{o(tr)}$(1)	Equivalent capacitance time related	V_{GS} = 0, V_{DS} = 0 to 760 V	-	16	-	pF
$C_{o(er)}$(2)	Equivalent capacitance energy related		-	6	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz open drain	-	16	-	Ω
Q_g	Total gate charge	V_{DD} = 760 V, I_D = 2 A V_{GS} =10 V *(see Figure 19)*	-	10	-	nC
Q_{gs}	Gate-source charge		-	1.5	-	nC
Q_{gd}	Gate-drain charge		-	8	-	nC

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
2. energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 475 V, I_D = 1 A, R_G = 4.7 Ω, V_{GS} = 10 V *(see Figure 18)*	-	8.5	-	ns
t_r	Rise time		-	13.5	-	ns
$t_{d(off)}$	Turn-off-delay time		-	20.5	-	ns
t_f	Fall time		-	32.5	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current		-		2	A
I_{SDM} (1)	Source-drain current (pulsed)		-		8	A
V_{SD} (2)	Forward on voltage	I_{SD} = 2 A, V_{GS} = 0	-		1.5	V
t_{rr}	Reverse recovery time	I_{SD} = 2 A, di/dt = 100 A/µs V_{DD}= 60 V *(see Figure 20)*	-	300		ns
Q_{rr}	Reverse recovery charge		-	1.15		µC
I_{RRM}	Reverse recovery current		-	7.6		A
t_{rr}	Reverse recovery time	I_{SD} = 2 A, di/dt = 100 A/µs V_{DD}= 60 V T_J = 150 °C *(see Figure 20)*	-	525		ns
Q_{rr}	Reverse recovery charge		-	1.90		µC
I_{RRM}	Reverse recovery current		-	7.2		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 µs, duty cycle 1.5%

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	I_{GS} = ± 1mA, I_D=0	30	-	-	V

The built-in back-to-back Zener diodes have been specifically designed to enhance not only the device's ESD capability, but also to make them capable of safely absorbing any voltage transients that may occasionally be applied from gate to source. In this respect, the Zener voltage is appropriate to achieve efficient and cost-effective protection of device integrity. The integrated Zener diodes thus eliminate the need for external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for DPAK and IPAK

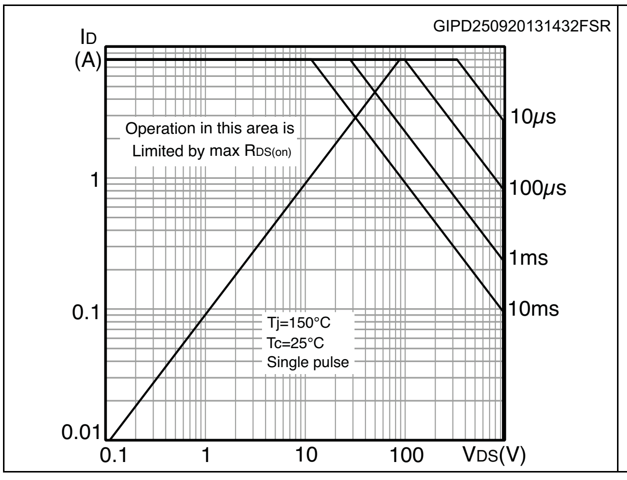


Figure 3. Thermal impedance for DPAK and IPAK

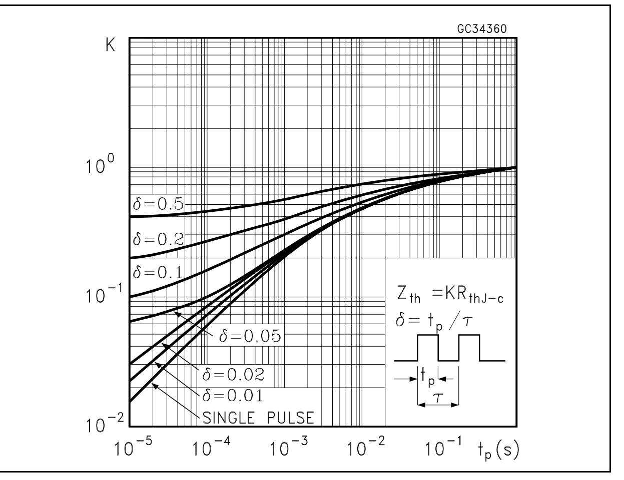


Figure 4. Safe operating area for TO-220FP

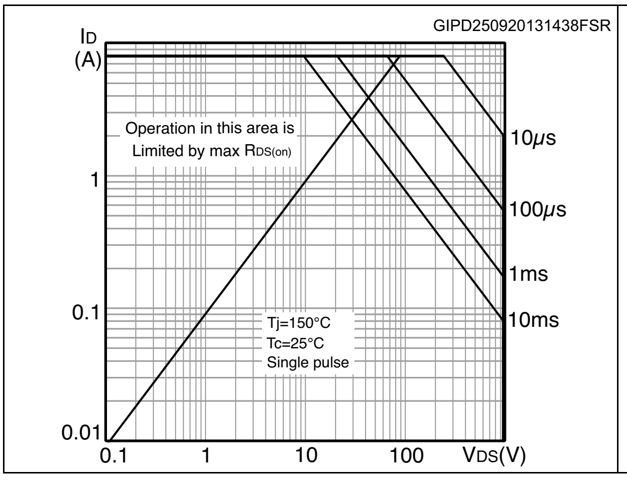


Figure 5. Thermal impedance for TO-220FP

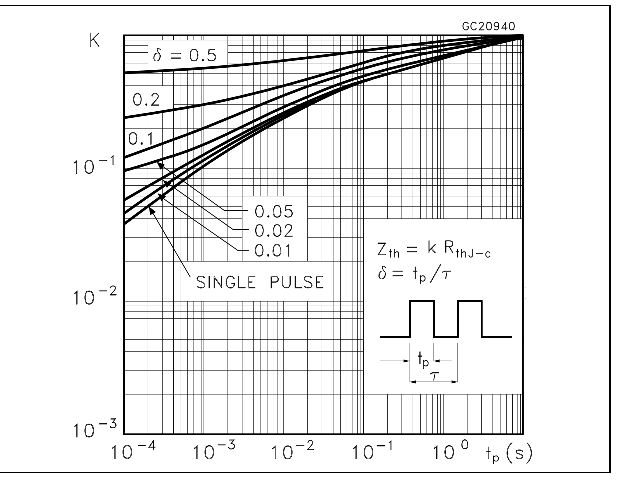


Figure 6. Safe operating area for TO-220

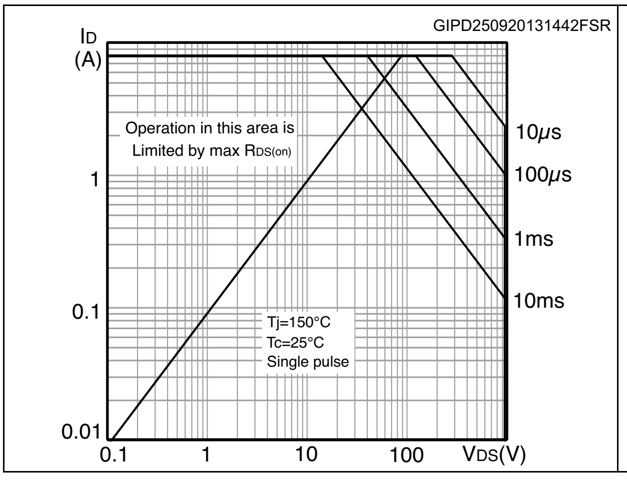


Figure 7. Thermal impedance for TO-220

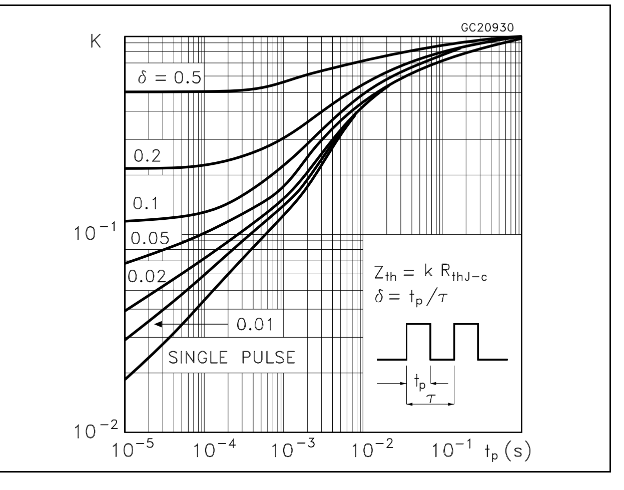


Figure 8. Output characteristics

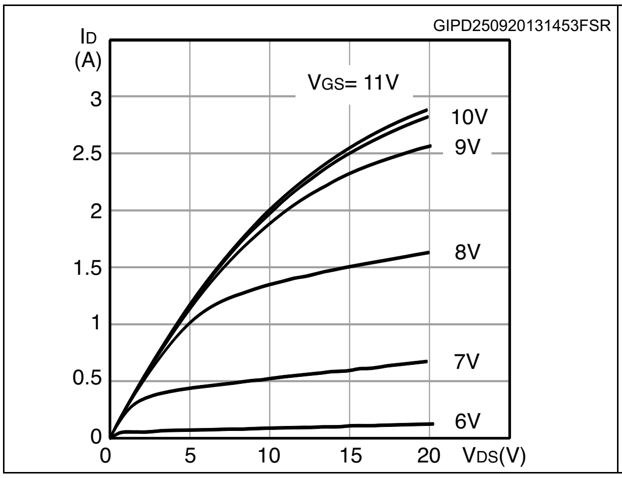


Figure 9. Transfer characteristics

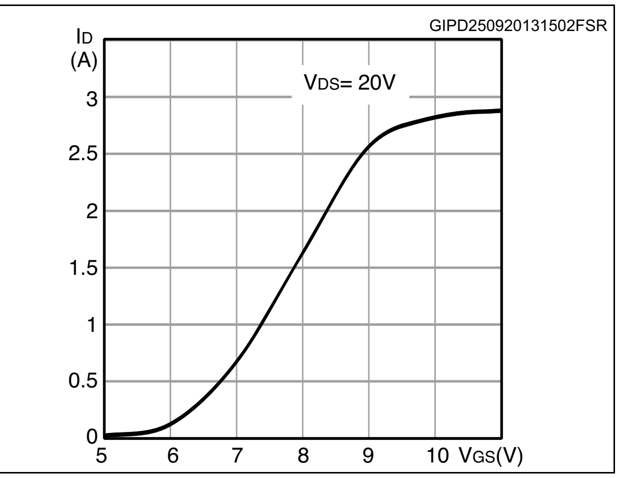


Figure 10. Gate charge vs gate-source voltage

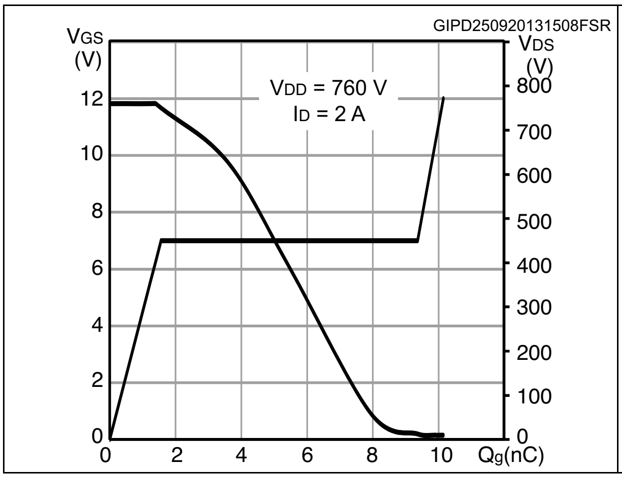


Figure 11. Static drain-source on-resistance

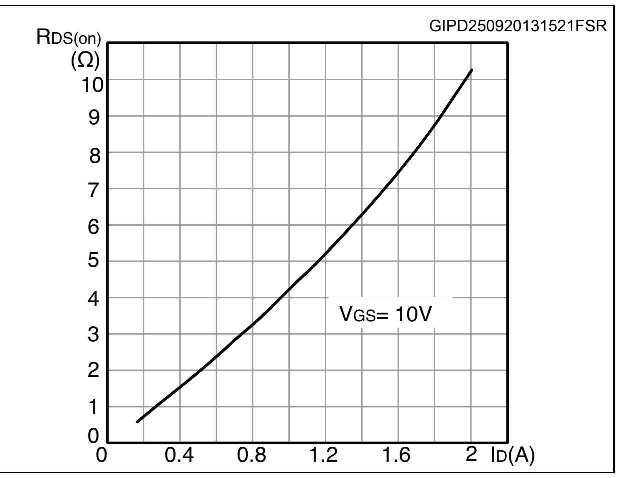


Figure 12. Capacitance variations

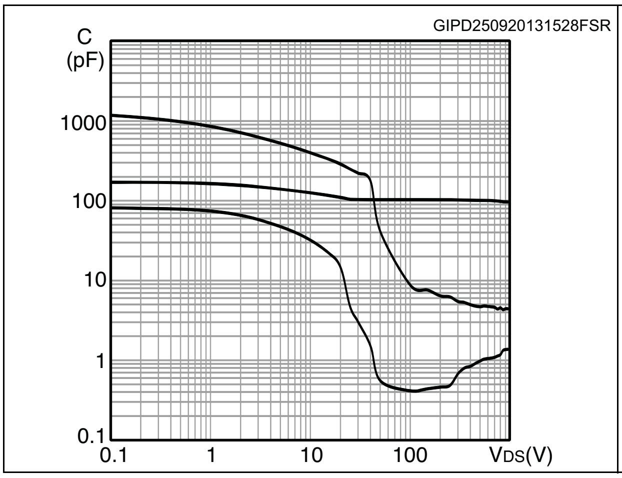


Figure 13. Output capacitance stored energy

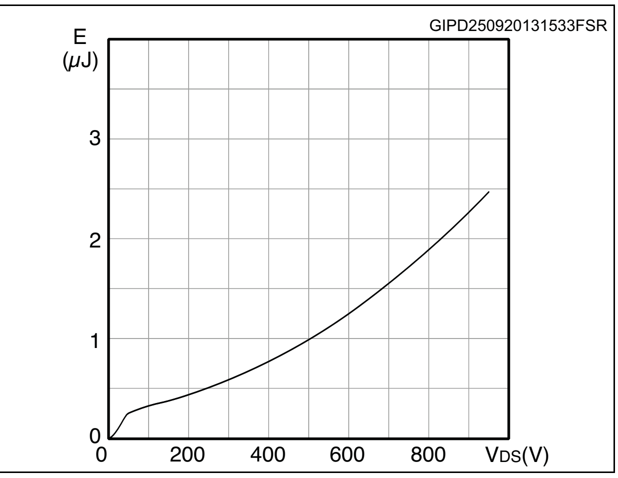


Figure 14. Normalized gate threshold voltage vs temperature

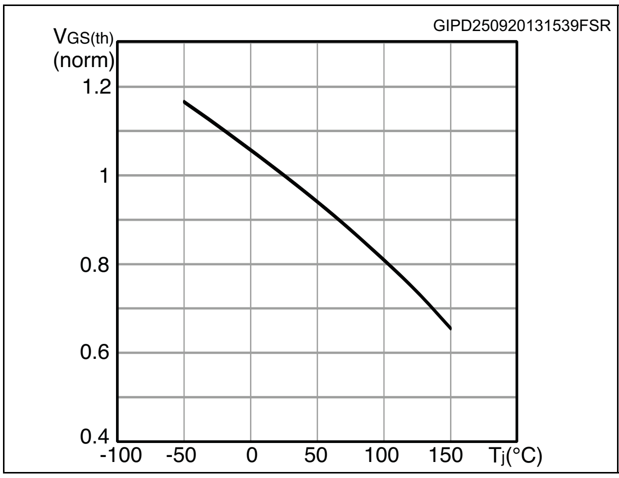


Figure 15. Normalized on-resistance vs temperature

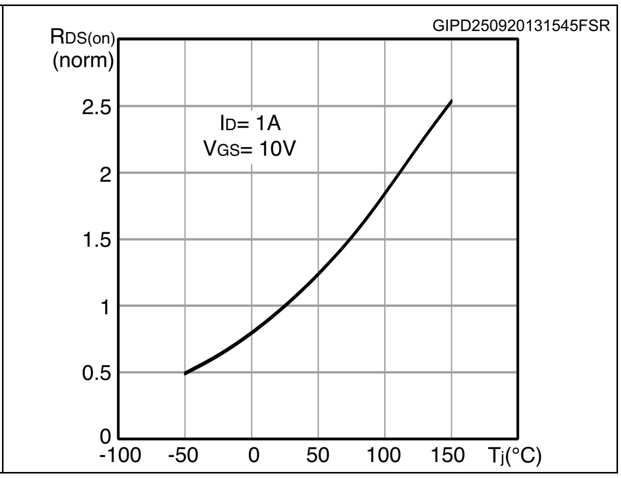


Figure 16. Source-drain diode forward characteristics

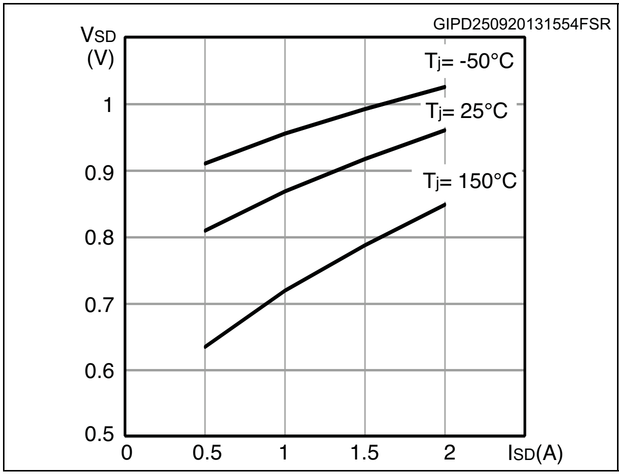
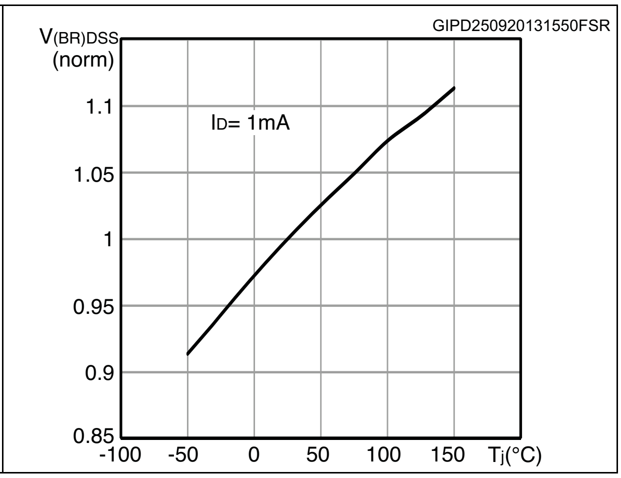


Figure 17. Normalized $V_{(BR)DSS}$ vs temperature



3 Test circuits

Figure 18. Switching times test circuit for resistive load

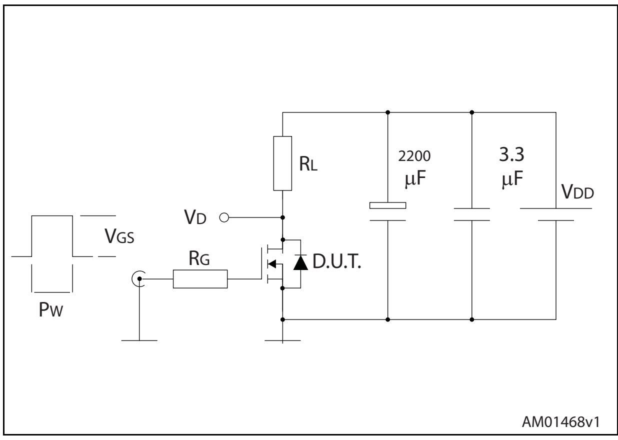


Figure 19. Gate charge test circuit

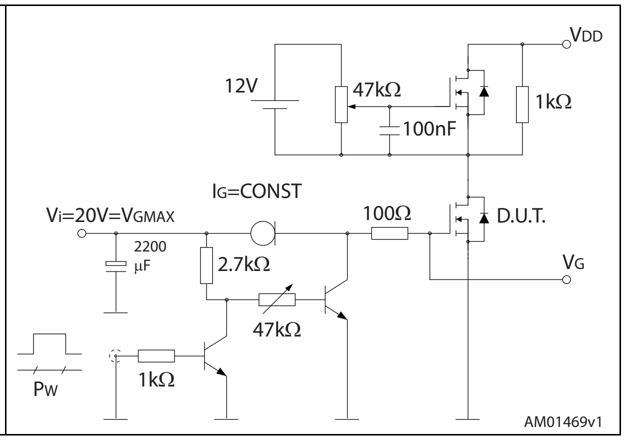


Figure 20. Test circuit for inductive load switching and diode recovery times

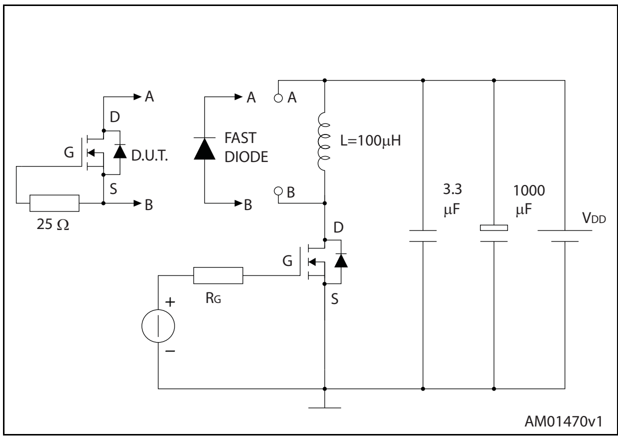


Figure 21. Unclamped inductive load test circuit

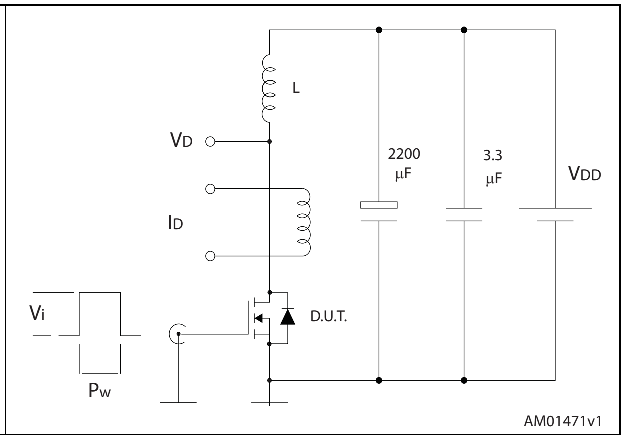


Figure 22. Unclamped inductive waveform

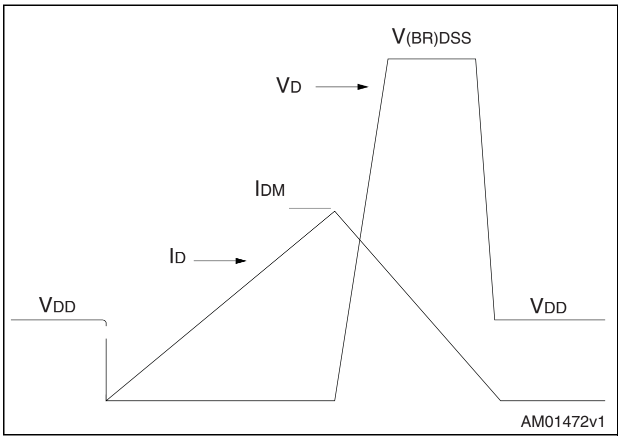
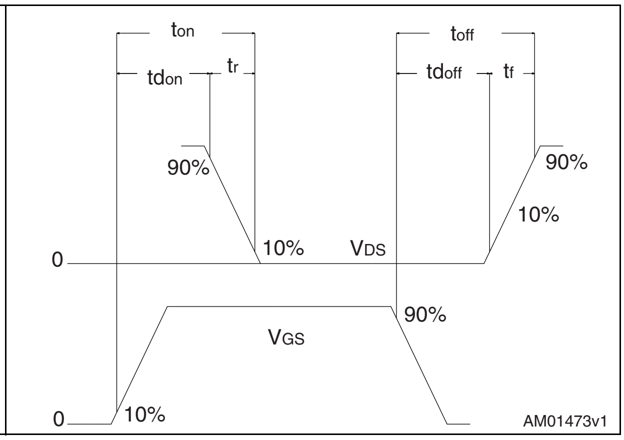


Figure 23. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

Table 9. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
(L1)		2.80	
L2		0.80	
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 24. DPAK (TO-252) type A drawing

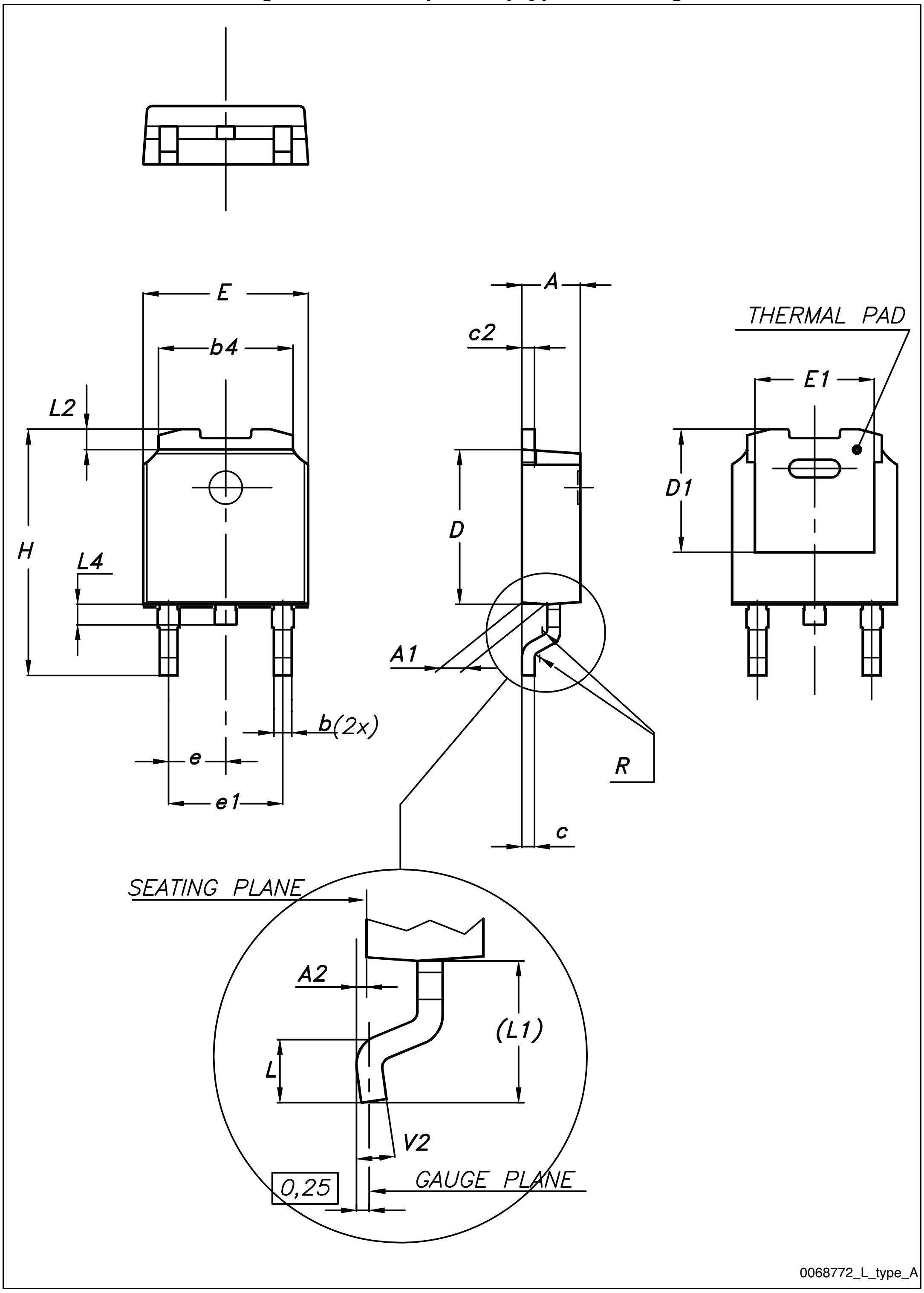
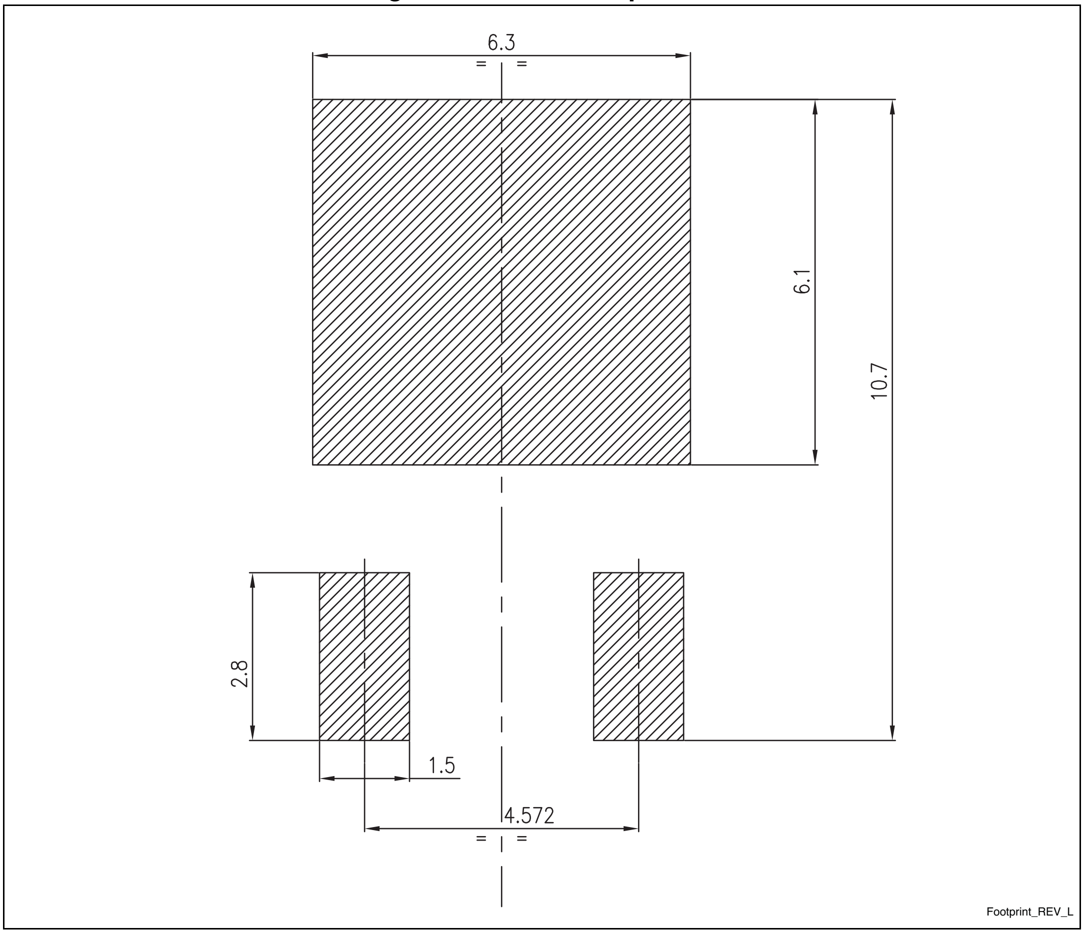


Figure 25. DPAK footprint [a]



a. All dimensions are in millimeters

Table 10. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 26. TO-220FP drawing

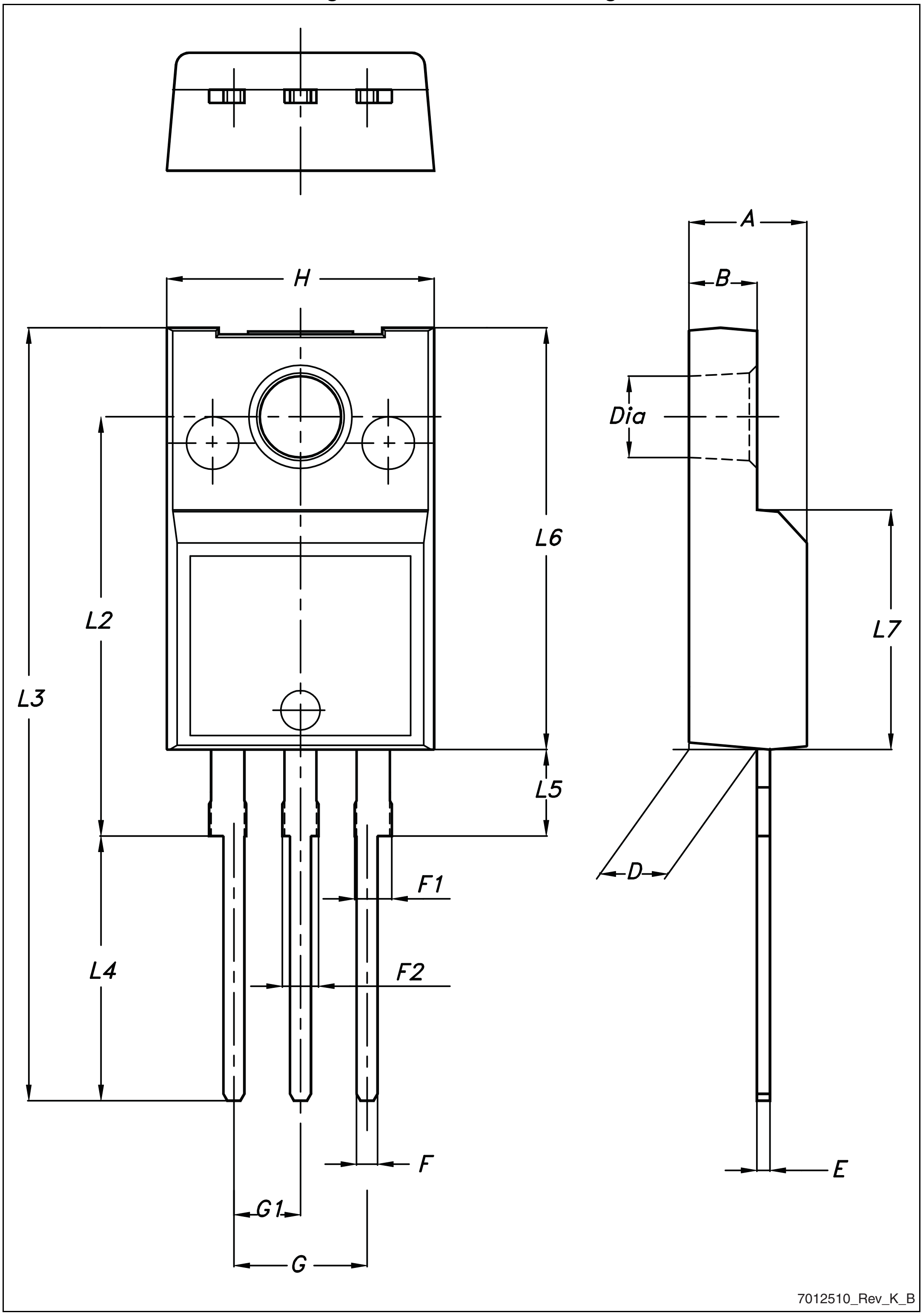


Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95

Figure 27. TO-220 type A drawing

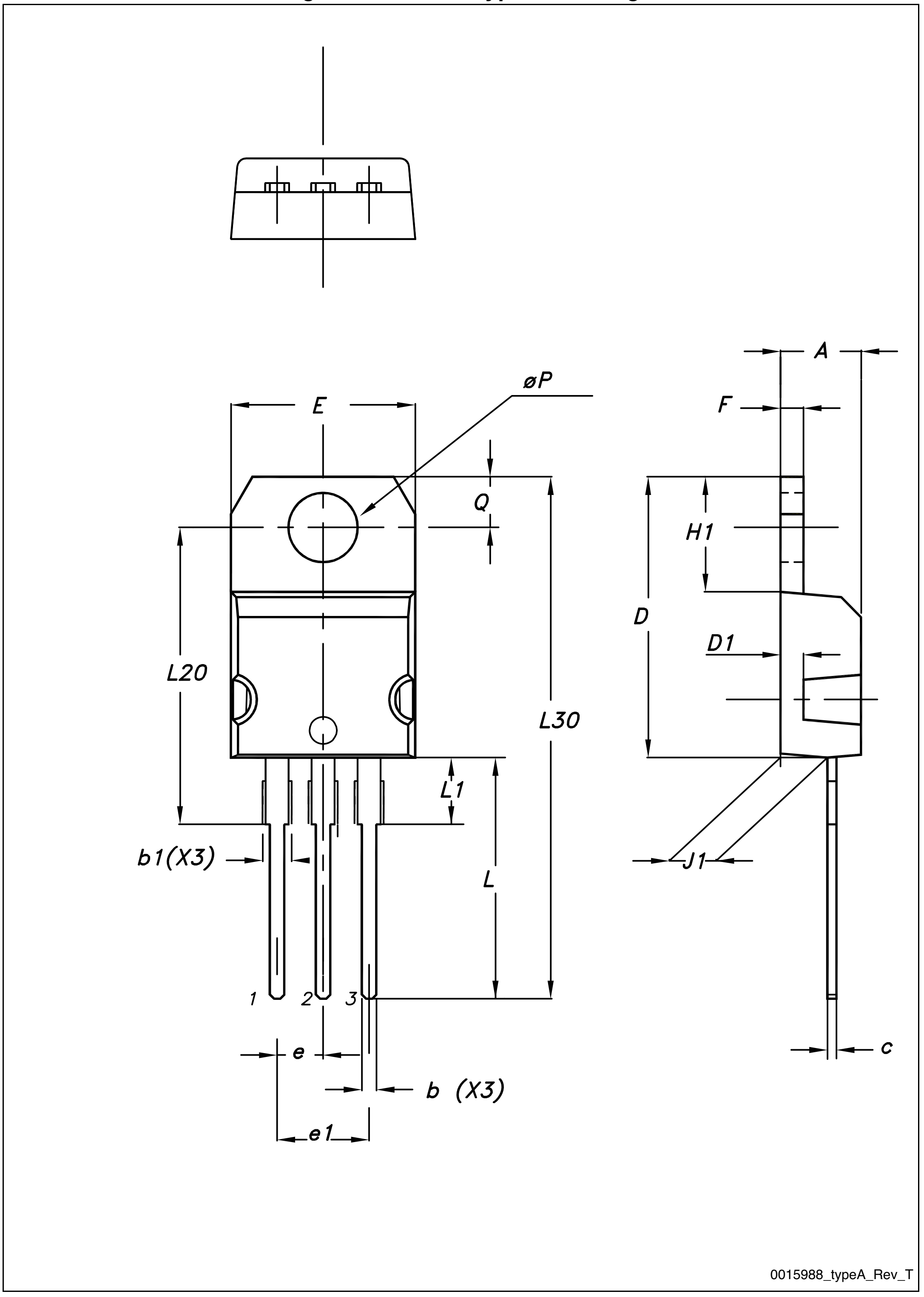
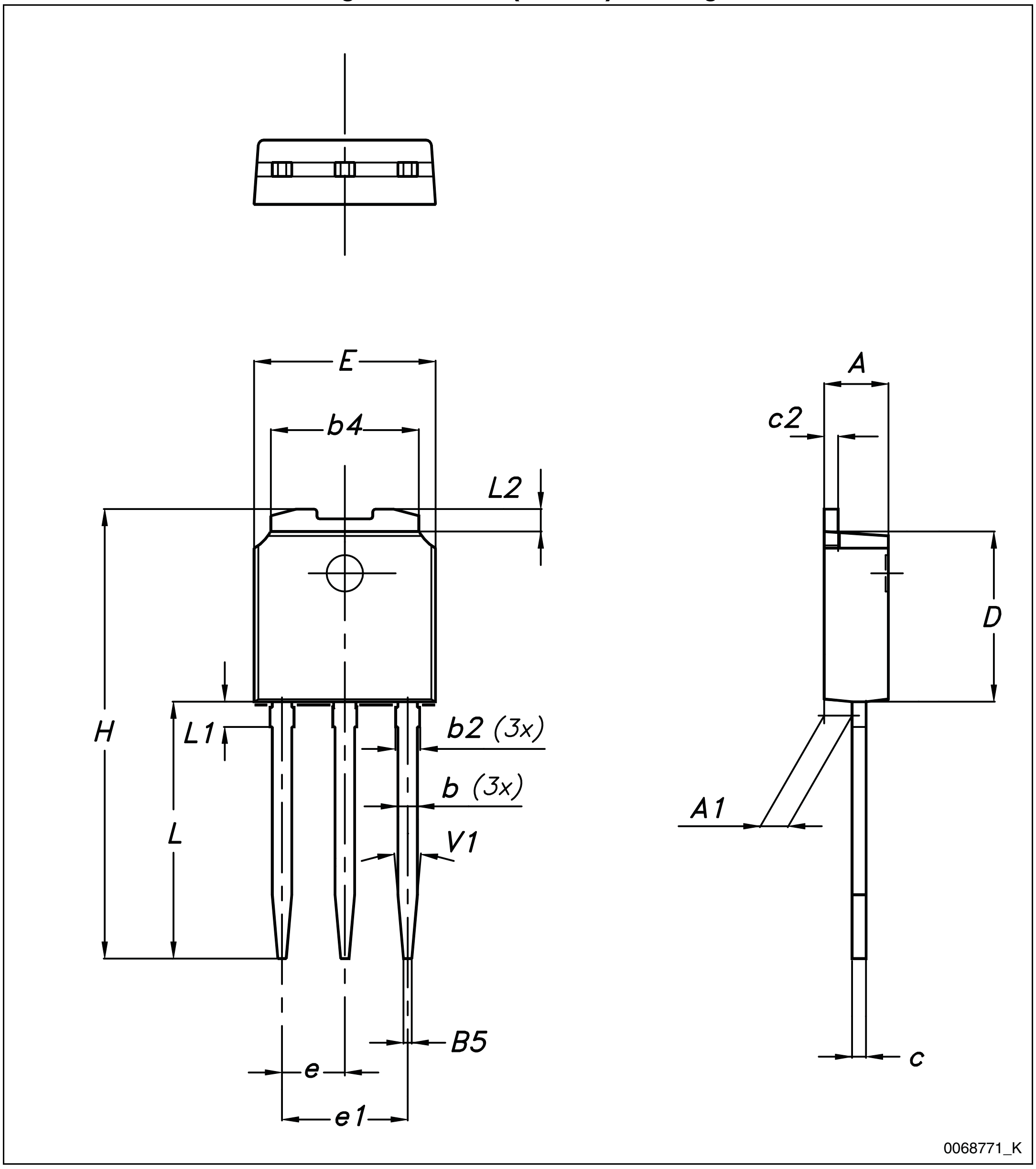


Table 12. IPAK (TO-251) mechanical data

DIM	mm.		
	min.	typ.	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

Figure 28. IPAK (TO-251) drawing



5 Packaging mechanical data

Table 13. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 29. Tape for DPAK (TO-252)

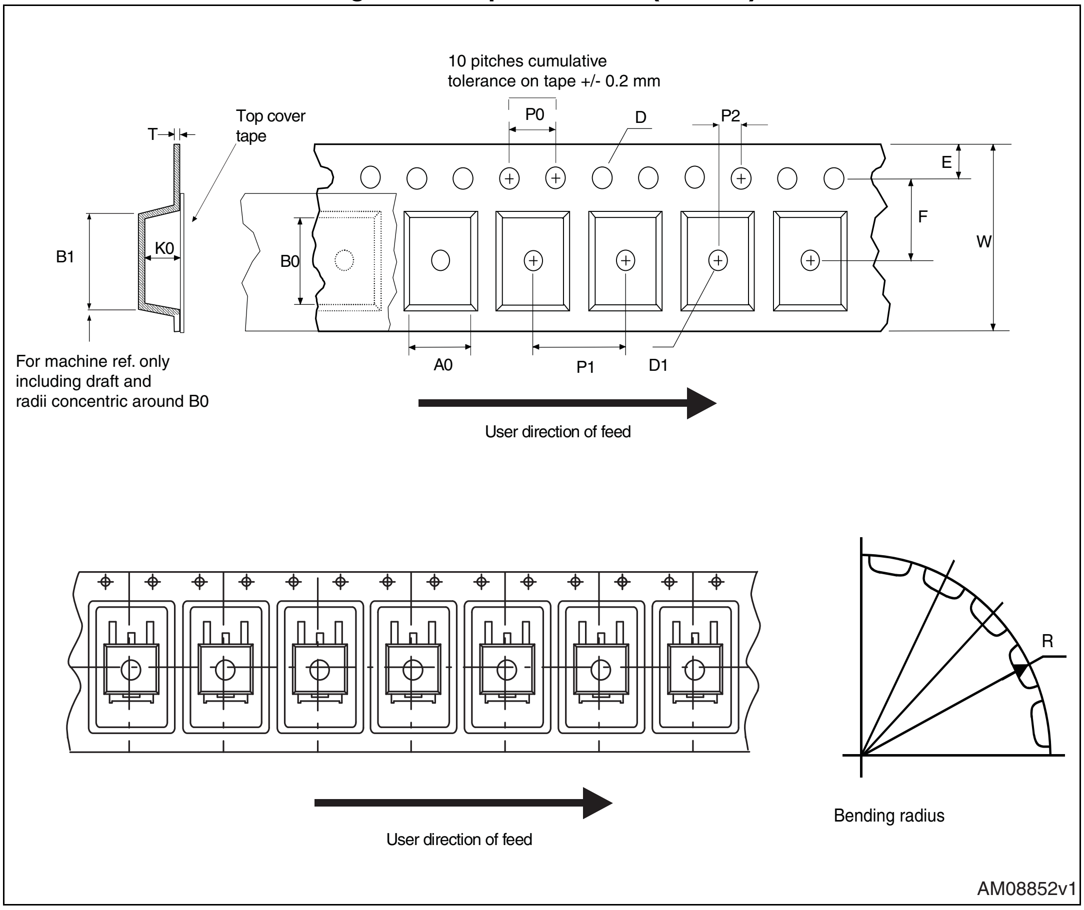
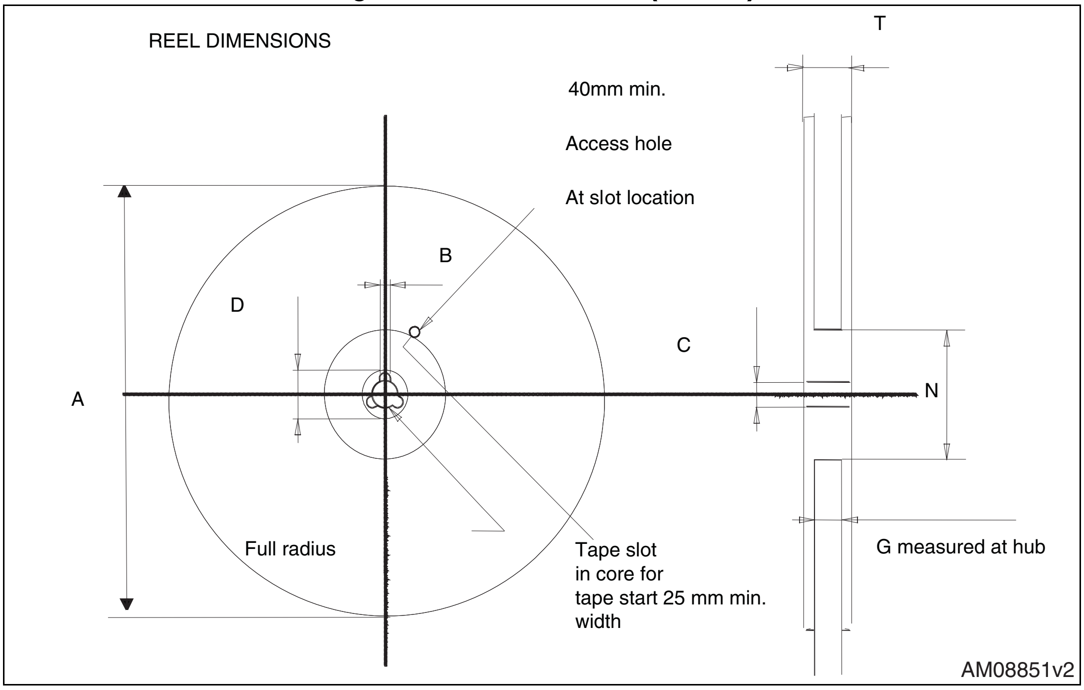


Figure 30. Reel for DPAK (TO-252)



6 Revision history

Table 14. Document revision history

Date	Revision	Changes
25-Sep-2013	1	First release.

Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.

Как с нами связаться

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